FORM PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION	DOCKET NUMBER SLA0778	APPLICATION NUMBER
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILE. DATE IF APPROP.

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO

OTHER DOCUMENTS

LT	Article entitled: Nucleation and interface formation mechanisms in atomic layer deposition of gate oxides; by Frank and Chabal, published in Applied Physics Letters, vol 82, No. 26, 30 June 2003
LT	Article entitled: Enhanced initial growth of atomic-layer-deposited metal oxided on hydrogen-terminated silicon; by Frank and Chabal, published in Applied Physics Letters, vol 83, No. 4, 28 July 2003
LT	Article entitled: Nucleation and growth of atomic layer deposited HfO_2 gate dielectric layers on chemical oxide (Si-O-H) and thermal oxide (SiO_2 or Si-O-N) underlayers; by Green *et al.*, published in Journal of Applied Physics, vol. 92, No. 12, 15 December 2002
LT	Article entitled: Atomic Layer Deposition of Hafnium Oxide Using Anhydrous Hafnium Nitrate; by Conley *et al.*, published in Electrochemical and Solid-State Letters, available electronically February 26, 2002
LT	Article entitled: Atomic layer deposition of thin hafnium oxide films using a carbon free precursor; by Conley and Solanki, published in Journal of Applied Physics, vol. 93, No. 1, 1 January 2003

EXAMINER	DATE CONSIDERED
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